L Number	Hits	Search Text	DB	Time stamp
-	887626	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:21
-	639571	mos$1fet or mis$1fet or fet or mos or pmos or nmos or field adj4 (transistor or device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:31
-	83577	(multiple or differen$2 or various) adj4 thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:32
-	2741827	insulat$4 or di$1electric or oxide or "sio.sub."$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:43
-	133420	gate adj5 (insulat$4 or di$1electric or oxide or "sio.sub."$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 14:16
-	484543	high adj3 (voltage or power)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:45
-	328173	low adj3 (voltage or power)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:46
-	978	gate with thick with (high adj3 (voltage or power))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:46
-	877	gate with thin with (low adj3 (voltage or power))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:47
-	301	(gate with thick with (high adj3 (voltage or power))) and (gate with thin with (low adj3 (voltage or power)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 14:49
-	300	((gate with thick with (high adj3 (voltage or power))) and (gate with thin with (low adj3 (voltage or power)))) and ((insulat$4 or di$1electric or oxide or "sio.sub."$1) or ((multiple or differen$2 or various) adj4 thickness))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:16
-	1461	438/591.ccls. or 438/585.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:04
-	1202	(438/591.ccls. or 438/585.ccls.) and (gate adj5 (insulat$4 or di$1electric or oxide or "sio.sub."$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:04
-	490	((438/591.ccls. or 438/585.ccls.) and (gate adj5 (insulat$4 or di$1electric or oxide or "sio.sub."$1))) and thick and thin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:05

-	156505	hf or hydrofluoric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:17
-	4732	hto or high adj2 temperature adj2 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 14:07
-	503341	etch$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:18
-	2493898	resistance or resistant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:19
-	4	(hf or hydrofluoric) same (hto or high adj2 temperature adj2 oxide) same etch$3 same (resistance or resistant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:22
-	2524462	etch$3 or removed	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:23
-	182885	bhf or boe or (hf or hydrofluoric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:25
-	101	(bhf or boe or (hf or hydrofluoric)) same (hto or high adj2 temperature adj2 oxide) same (etch$3 or removed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 16:26
-	4732	hto or high adj2 temperature adj2 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 14:08
-	10404321	benefit or advantag$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 14:08
-	140	(hto or high adj2 temperature adj2 oxide) with (benefit or advantag$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 14:08
-	133420	gate adj5 (insulat$4 or di$1electric or oxide or "sio.sub."$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 14:18
-	302	(hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat$4 or di$1electric or oxide or "sio.sub."$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 14:19
-	228	(hto or high adj2 temperature adj2 oxide) with teos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/25 14:20

-	25	((hto or high adj2 temperature adj2 oxide) with (gate adj5 (insulat$4 or di$1electric or oxide or "sio.sub."$1))) and ((hto or high adj2 temperature adj2 oxide) with teos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/25 14:20